

Surname, name » Andrejus Geizutis

Science name & degree: associated professor, doctor

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[The list of publications \(from 2000\)](#)

[Personal WEB pages:](#)

Subjects delivered:

- Electronic measurements, lectures and laboratory works (in Lithuanian),
- Measurements in telecommunication systems, lectures and laboratory works (in Lithuanian),
- Electronics fundamentals, laboratory works (in English)
- Electronic devices, lectures and laboratory works (in English)

More information:

Scientific interests: Semiconductor physics:

- Fabrication and characterization of semiconductor devices,
- THz frequency range photoconductor emitters and detectors,
- Semiconductor photodetectors (UTC, PIN),
- Semiconductor laser diodes,
- Automation of measurements (experience in Labview)

Foreign languages: English, Russian.

Education:

- Doctor of Science, Semiconductor Physics Institute (SPI), 2000.
- Master of Science, Vilnius Gediminas Technical University (VGTU), 1994.
- Radio Engineer, VGTU, 1993.

Professional activity:

- Associated professor, VGTU, 2009.
- Lecturer, VGTU, 2008.
- Associated professor, VGTU, 2006.
- Scientific worker, SPI, 2000.
- Doctoral student, SPI, 1994.
- Assistant, VGTU, 1994.

Publications

3 booklets for students, 18 papers in scientific journals and conference proceedings.

The main publications:

- Voltage switching and oscillations in a single barrier heterostructure hot-electron diode, *J. Appl. Phys.*, 1998, Vol. 84, No 7, p. 3980-3985 (coauthor, in English).
- Carrier recombination properties in low-temperature-grown and ino-implanted GaAs, *Lith. J. Phys.*, V. 45, Nr. 4, 2005, p. 249-255. (coauthor, in English).
- Terahertz radiation emitters and detectors, *Optical Materials*, V. 30, Nr. 5, 2008, p. 786-788). (coauthor, in English).
- Growth and characterization of UTC photo-diodes containing GaAs_{1-x}Bi_x absorber layer, *Solid State Elec.*, 2014. Vol. 99, p.101-103 (coauthor, in English).
- Multi-quantum well Ga(AsBi)/GaAs laser diodes with more than 6% of bismuth, *El. Letters*, 2014, Vol. 50, No 16, p. 1155 – 1157 (coauthor, in English).